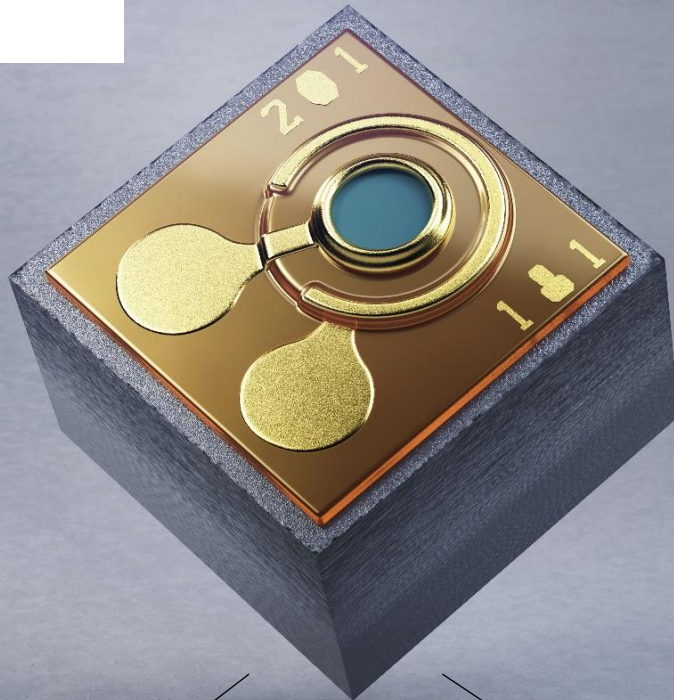


PIN Photodiode

14 Gbps
850 nm



High speed up to
14 Gbps

GaAs PIN
Photodiode

Available in
1x1, 1x4, 1x12

Low bias voltage

Low dark current

4 inch wafer

TRUMPF

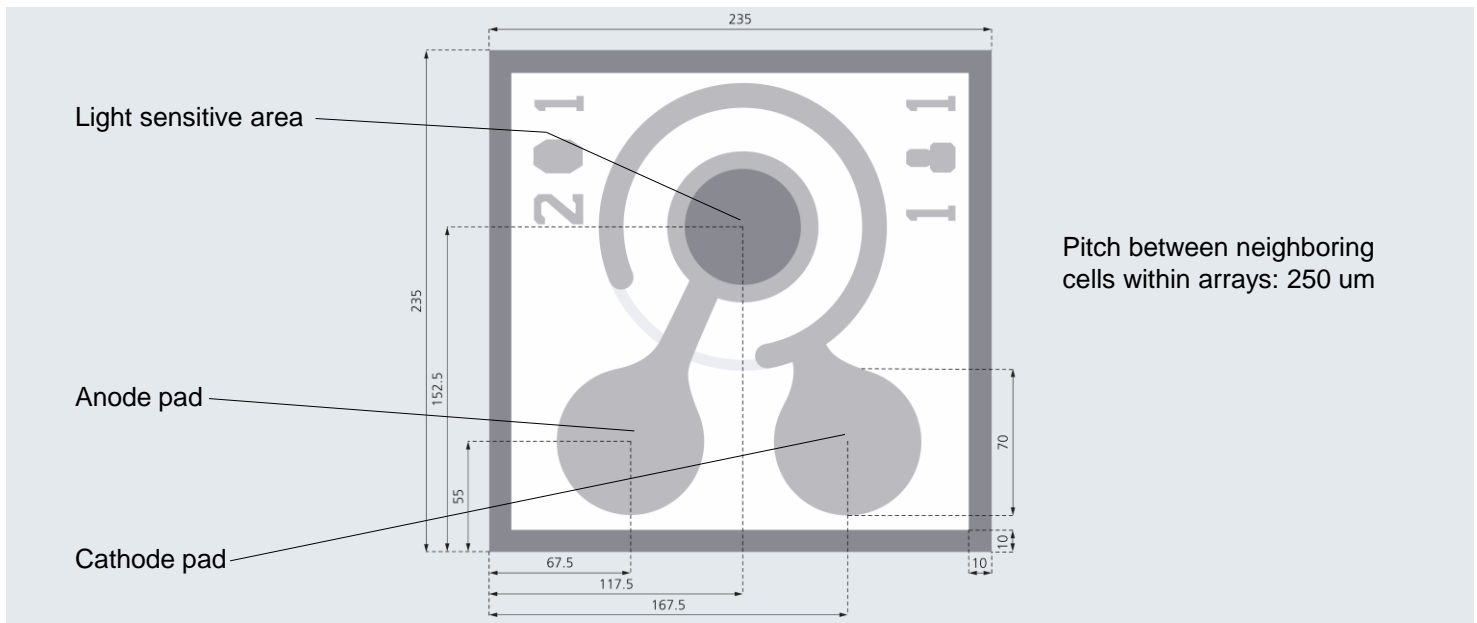


Datasheet: 14 Gbps PIN Photodiode

Electro-Optical Characteristics (T = 25°C unless otherwise stated)

Parameter	Symbol	Units	Min	Typ	Max	Test Condition
Responsivity	R	A/W		0.6		
Active area diameter	d_{act}	μm		55		
Dark current 1	I_{d1}	nA		0.02	0.2	$U_{bias} = -2\text{ V}$
Dark current 2	I_{d2}	μA			I	$U_{bias} = -20\text{ V}$
Capacitance	C	fF		180		$U_{bias} = -2\text{ V}$
Modulation bandwidth	$f_{3\text{ dB}}$	GHz		12		50 Ohm load, -3dB, $U_{bias} = -2\text{ V}$
Wavelength range	λ	nm	840		860	

Dimensions of 14G Photodiode:



Units: μm

Product variants

Type	Single chip	1 x 4 line array	1 x 12 line array
Part number	TPD-14(01)-850-A0	TPD-14(04)-850-A0	TPD-14(12)-850-A0
Ordering number	ULMPIN-14-TT-N0101U (PD07)	ULMPIN-14-TT-N0104U (PD07)	ULMPIN-14-TT-N0112U (PD07)
Dimensions	235 x 235 x 150 μm	235 x 985 x 150 μm	235 x 2985 x 150 μm
Wiring		Electrically separated channels	Electrically separated channels

For more information visit
www.trumpf.com/s/VCSEL-solutions

Safety information:

- Invisible laser radiation / avoid beam exposure / class 3B laser product
- Electrostatic sensitive devices / observe precautions for handling

TRUMPF Photonic Components GmbH

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January 2022

